Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3697	((257/330) or (438/259,270,273, 589,438)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 12:59
S2	2541	S1 and (trench$2 or groove$2 or recess$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:00
S3	2441	S2 and (@ad<"20040303" or @rlad<"20040303")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:02
S4	2188	S3 and (source or drain or gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:06
S5	955	S4 and (anneal$4 or heat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:06
S6	155	S5 and (thermal near4 diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:10
S7	259	S5 and (anneal$4 with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:50
S8	26	("5831301"|"5940717"|"5945704"|" 6018174"|"6063657"|"6066527"|"60 80618"|"6144054"|"6437381"|"6455 378"|"6465325"|"6469345"|"663038 9").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:50
S10	99	(anneal$4 near4 temperature) with "1150"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 14:57
S11	616	(anneal$4 near4 temperature) with ("1150" or "1100" or "1200" or "1250")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 15:01

S12	255	(anneal$4 near4 temperature) with ("1150" or "1100" or "1200" or "1250") and (semiconductor and (source or drain or gate or mosfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 15:15
S13	123	(anneal$4 near4 temperature) with ("1150" or "1200" or "1250") and (semiconductor and (source or drain or gate or mosfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 15:15
S14	11	("5435888" | "5902127" | "6010948" | "6020230" | "6214698" | "6265281").PN. OR ("6465325"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:08
S15	10713	(rapid adj thermal adj anneal$5)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S16	519	S15 with (insulat$4 or dielectric)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S17	13	S16 with (damage or repair or fix)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S18	169	S16 with (gate)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:14
S19	14479	(rapid adj thermal adj anneal$5) or RTA	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S20	772	S19 with (insulat$4 or dielectric)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S21	20	S20 with (damage or repair or fix)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/30 10:17
S22	7	S21 not S17	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 10:13
S23	2320	anneal$4 with (inert near2 gas)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 10:13
S24	1121	anneal$4 with ((inert near2 gas) with atmosphere)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 10:13
S25	98	anneal$4 with ((inert near2 gas) with atmosphere) and mosfet	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 11:03
S26	998	gate with (T-shaped)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 11:11

S27	207	gate with (T-shaped) and mosfet	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 11:12
S28	71	(gate with (T-shaped)) same (ang or angstrom$2 or um or micrometer$2)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 11:21
S29	11	(gate with (T-shaped)) same (ang or angstrom$2 or um or micrometer$2) and overlap	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/03 11:22